

### Solid State Devices, Inc.

14701 Firestone Blvd \* La Mirada, CA 90638 Phone: (562) 404-4474 \* Fax: (562) 404-1773 ssdi@ssdi-power.com \* www.ssdi-power.com

## **Designer's Data Sheet**

## Part Number/Ordering Information 1/

#### 1N80

#### **Package Type**

\_\_ = Axial Leaded SMS = Surface Mount Square Tab

Device Type (VRWM)

**18** = 100 V **19** = 150 V

**20** = 200 V

## 1N8018 thru 1N8020 SERIES

1 AMP 100 - 200 VOLTS 9 nsec HYPER FAST SOFT RECOVERY RECTIFIER

#### **FEATURES:**

- Hyper fast reverse recovery time 9 ns max
- Low forward voltage drop
- Low reverse leakage current
- Avalanche breakdown
- Void free ceramic frit glass construction
- High temperature category I eutectic metallurgical bond
- · Hermetically sealed
- · Solid silver lead
- Excellent liquid-to-liquid cryogenic thermal shock performance
- Available in axial & square tab versions
- · For high efficiency applications
- TX, TXV, and S-level screening available<sup>2/</sup>
- Available as a QPL product per MIL-PRF-19500/769
- Replacement for 1N6638, 1N6642 and 1N5806

| MAXIMUM RATINGS 3/                                                                                                                                |                            |                                        |                   |       |
|---------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------|----------------------------------------|-------------------|-------|
| RATING                                                                                                                                            |                            | SYMBOL                                 | VALUE             | UNIT  |
| Peak Repetitive Reverse Voltage<br>DC Blocking Voltage                                                                                            | 1N8018<br>1N8019<br>1N8020 | $oldsymbol{V_{RWM}}{oldsymbol{V_{R}}}$ | 100<br>150<br>200 | Volts |
| Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, T <sub>C</sub> = 25°C)                                                       |                            | lo                                     | 1                 | Amp   |
| Peak Surge Current (8.3 msec Pulse, Half Sine Wave Superimposed on Io, allow junction to reach equilibrium between pulses, T <sub>C</sub> = 25°C) |                            | I <sub>FSM</sub>                       | 20                | Amps  |
| Operating & Storage Temperature                                                                                                                   |                            | $T_{\text{OP}}$ and $T_{\text{STG}}$   | -65 to +175       | °C    |
| Thermal Resistance SMS- Junction to End Tab Axial- Junction to Lead @ .375"                                                                       |                            | R <sub>θJE</sub><br>R <sub>θJL</sub>   | 20<br>80          | °C/W  |

#### **NOTES:**

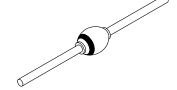
1/ For Ordering Information, Price, and Availability- Contact Factory.

**2**/ Screening Based on MIL-PRF-19500. Screening Flows Available on Request.

3/ Unless Otherwise Specified, All Electrical Characteristics @25°C.

**Axial Leaded** 

SMS







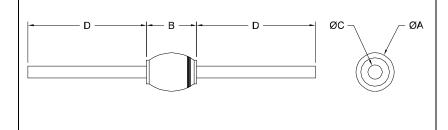
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# 1N8018 thru 1N8020 **SERIES**

| ELECTRICAL CHARACTERISTICS 3/ CHARACTERISTICS                                    |                                                                                                                                                                                                                      | SYMBOL                                                                                                         | LIMIT                                              | UNIT |
|----------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------|----------------------------------------------------|------|
| Maximum Instantaneous Forward Voltage Drop (Pulsed, T <sub>A</sub> = 25°C)       | $\bigcirc$ I <sub>F</sub> = 1mA<br>$\bigcirc$ I <sub>F</sub> = 10mA<br>$\bigcirc$ I <sub>F</sub> = 100mA<br>$\bigcirc$ I <sub>F</sub> = 200mA<br>$\bigcirc$ I <sub>F</sub> = 500mA<br>$\bigcirc$ I <sub>F</sub> = 1A | V <sub>F1</sub><br>V <sub>F2</sub><br>V <sub>F3</sub><br>V <sub>F4</sub><br>V <sub>F5</sub><br>V <sub>F6</sub> | 0.575<br>0.700<br>0.800<br>0.850<br>0.900<br>0.975 | Vdc  |
| Maximum Instantaneous Forward Voltage Drop (Pulsed, T <sub>A</sub> = 150°C)      | @ I <sub>F</sub> = 10mA<br>@ I <sub>F</sub> = 100mA                                                                                                                                                                  | V <sub>F7</sub><br>V <sub>F8</sub>                                                                             | 0.50<br>0.62                                       | Vdc  |
| Maximum Instantaneous Forward Voltage Drop (Pulsed, T <sub>A</sub> = -55°C)      | @ I <sub>F</sub> = 10mA<br>@ I <sub>F</sub> = 100mA                                                                                                                                                                  | $ m V_{F9}  m V_{F10}$                                                                                         | 0.81<br>0.92                                       | Vdc  |
| Minimum Breakdown Voltage $I_R$ = 100 $\mu A$                                    | 1N8018<br>1N8019<br>1N8020                                                                                                                                                                                           | $BV_R$                                                                                                         | 110<br>165<br>220                                  | Vdc  |
| Maximum Reverse Leakage Current (300 $\mu$ s Pulse Minimum , $T_A$ = 25°C)       | $\textcircled{Q}$ $V_R = 20V$<br>$\textcircled{Q}$ $V_R = 75V$<br>$\textcircled{Q}$ $V_R = \max \text{ rated}$                                                                                                       | I <sub>R1</sub><br>I <sub>R2</sub><br>I <sub>R3</sub>                                                          | 50<br>75<br>150                                    | nA   |
| Maximum Reverse Leakage Current (300 μs Pulse Minimum , T <sub>A</sub> = 150°C)  | @ $V_R = 20V$<br>@ $V_R = 75V$<br>@ $V_R = \max \text{ rated}$                                                                                                                                                       | I <sub>R4</sub><br>I <sub>R5</sub><br>I <sub>R6</sub>                                                          | 50<br>75<br>150                                    | μΑ   |
| Maximum Junction Capacitance $(T_A = 25^{\circ}C, f = 1MHz) V_R = 0V$            |                                                                                                                                                                                                                      | $C_{J1}$                                                                                                       | 14                                                 | pf   |
| Maximum Junction Capacitance $(T_A = 25^{\circ}C, f = 1MHz) V_R = 1.5V$          |                                                                                                                                                                                                                      | C <sub>J2</sub>                                                                                                | 10                                                 | pf   |
| Maximum Junction Capacitance $(T_A = 25^{\circ}C , f = 1 MHz) V_R = 10V$         |                                                                                                                                                                                                                      | C <sub>J3</sub>                                                                                                | 6                                                  | pf   |
| Maximum Reverse Recovery Time ( $I_F = 50$ mA, $I_R = 100$ mA, $I_{RR} = 25$ mA) |                                                                                                                                                                                                                      | t <sub>rr</sub>                                                                                                | 9                                                  | nsec |
| Maximum Forward Recovery Time (I <sub>F</sub> = 50 mA)                           |                                                                                                                                                                                                                      | t <sub>fr</sub>                                                                                                | 18                                                 | nsec |

|     | AXIAL |       |
|-----|-------|-------|
| DIM | MIN   | MAX   |
| Α   | .056" | .075" |
| В   | .125" | .140" |
| С   | .018" | .022" |
| D   | 1.00" | 1.50" |



| SMS |       |       |  |  |
|-----|-------|-------|--|--|
| DIM | MIN   | MAX   |  |  |
| Α   | .070" | .085" |  |  |
| В   | .168" | .200" |  |  |
| С   | .019" | .028" |  |  |
| D   | .001" |       |  |  |

